

isc Silicon PNP Power Transistor

2SB520

DESCRIPTION

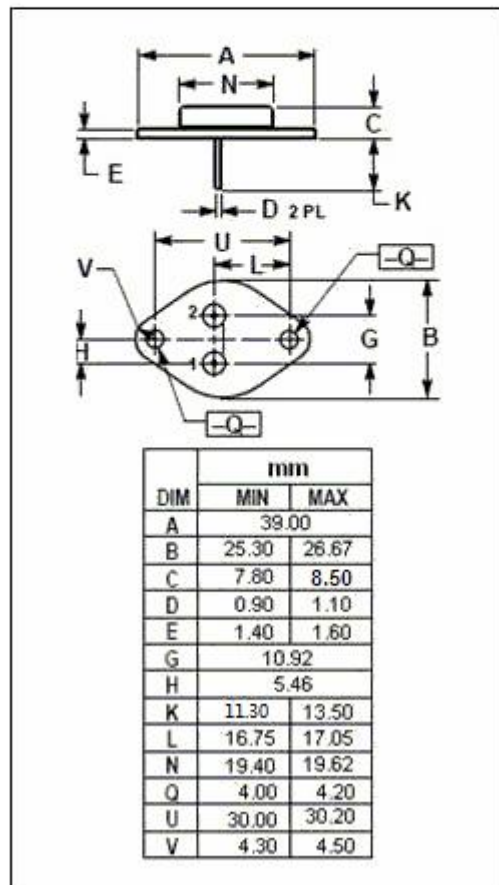
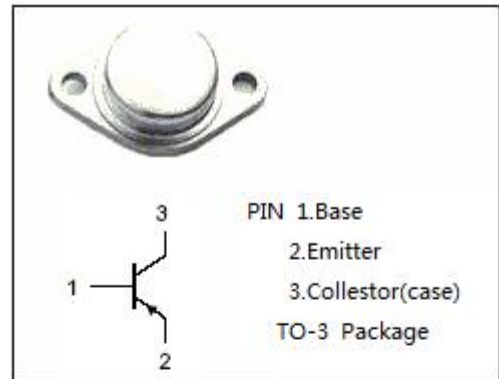
- Collector-Emitter Sustaining Voltage-
: $V_{CE(SUS)} = -140V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -1.0V(\text{Max.}) @ I_c = -7A$
- Wide area of safe operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general-purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-140	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_c	Collector Current-Continuous	-12	A
P_c	Collector Power Dissipation @ $T_c=25^\circ C$	100	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$



isc Silicon PNP Power Transistor**2SB520****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -10mA; I _B = 0	-140			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-8			V
V _{(BR)CBO}	Collector-Base breakdown voltage	I _C =-1mA; I _E = 0	-200			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -7A; I _B = -0.7A			-1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -7A; I _B = -0.7A			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -200V; I _E = 0			-100	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = -140V; I _B = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -8V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -5A; V _{CE} = -2V	50			
f _T	Current-Gain—Bandwidth Product	I _C =-0.5A ; V _{CE} = -10V		15		MHz